N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
40	0.025 at V_{GS} = 10 V	6.0	4.0
	0.030 at V_{GS} = 4.5 V	4.5	

FEATURES

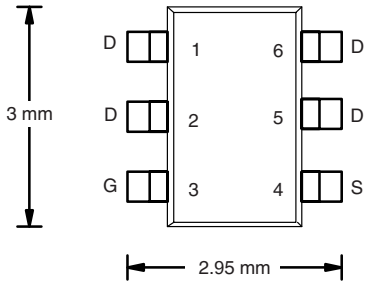
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

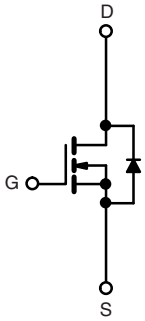
RoHS COMPLIANT

APPLICATIONS

- CCFL Inverter
- DC/DC Converter
- HDD

TSOP-6
Top View





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	6.0	A
	T_C = 70 °C		4.5	
	T_A = 25 °C		3.0[b, c]	
	T_A = 70 °C		2.0[b, c]	
Pulsed Drain Current (10 µs Pulse Width)		I_{DM}	18	
Source-Drain Current Diode Current	T_C = 25 °C	I_S	2.0	
	T_A = 25 °C		1.4[b, c]	
Pulsed Source-Drain Current		I_{SM}	20	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	10	
Single Pulse Avalanche Energy		E_{AS}	5	
Maximum Power Dissipation	T_C = 25 °C	P_D	1.3	W
	T_C = 70 °C		0.9	
	T_A = 25 °C		1.0[b, c]	
	T_A = 70 °C		0.75[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typ.**	**Max.**	**Unit**
Maximum Junction-to-Ambient[b, d]	t ≤ 10 s	R_{thJA}	49	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady-State	R_{thJF}	30	40	

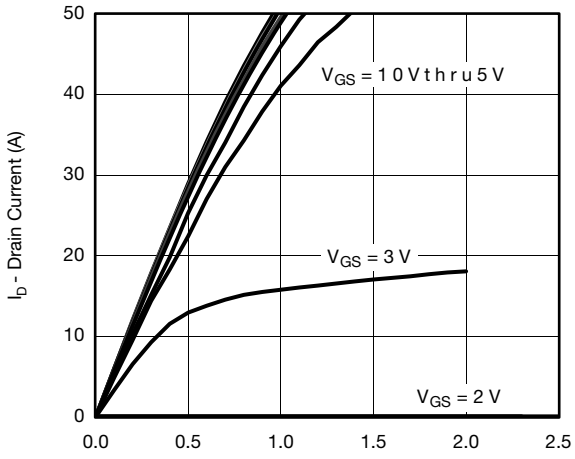
Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under steady state conditions is 120 °C/W.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.[a]**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	40			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		49		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.2		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D= 250 µA	1.0		2.0	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V			1	µA
		V_{DS} = 40 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	20			A
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 7.0A		0.025		Ω
		V_{GS} = 4.5 V, I_D = 6.0A		0.030		
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 7.0A		35		S
Dynamic[a]						
Input Capacitance	C_{iss}	V_{DS} = 20 V, V_{GS} = 0 V, I_D = 1 MHz		680		pF
Output Capacitance	C_{oss}			50		
Reverse Transfer Capacitance	C_{rss}			22		
Total Gate Charge	Q_g	V_{DS} = 20 V, V_{GS} = 10 V, I_D = 7.0 A		9.0		nC
		V_{DS} = 20 V, V_{GS} = 4.5 V, I_D = 7.0 A		4.5		
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			1.5		
Gate Resistance	R_g	f = 1 MHz	0.6	2.7	5.4	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 20 V, R_L = 2 Ω I_D ≅ 7.0 A, V_{GEN} = 10 V, R_g = 1 Ω		7	14	ns
Rise Time	t_r			9	18	
Turn-Off Delay Time	$t_{d(off)}$			16	32	
Fall Time	t_f			8	16	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 20 V, R_L = 2 Ω I_D ≅ 7.0 A, V_{GEN} = 4.5 V, R_g = 1 Ω		12	24	
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			13	26	
Fall Time	t_f			8	16	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C		6		A
Pulse Diode Forward Current[a]	I_{SM}			18		
Body Diode Voltage	V_{SD}	I_S = 3 A		0.77	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 5 A, dI/dt = 100 A/µs, T_J = 25 °C		15	30	ns
Body Diode Reverse Recovery Charge	Q_{rr}			7.5	15	nC
Reverse Recovery Fall Time	t_a			9		ns
Reverse Recovery Rise Time	t_b			6		

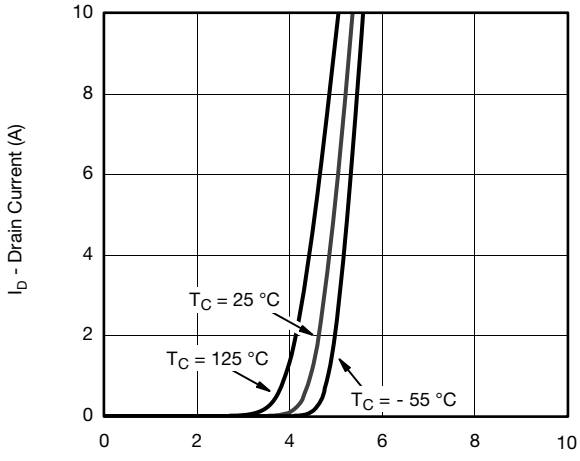
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

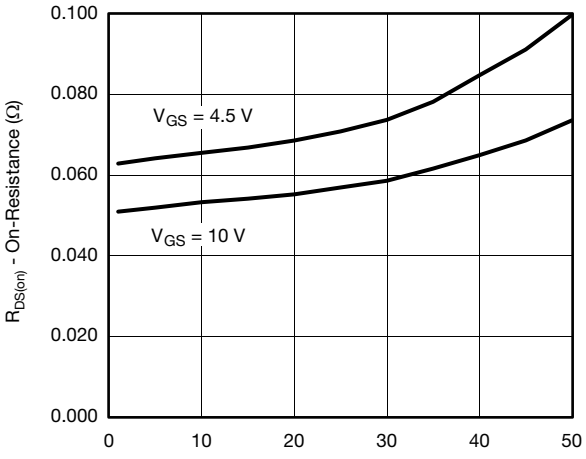
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



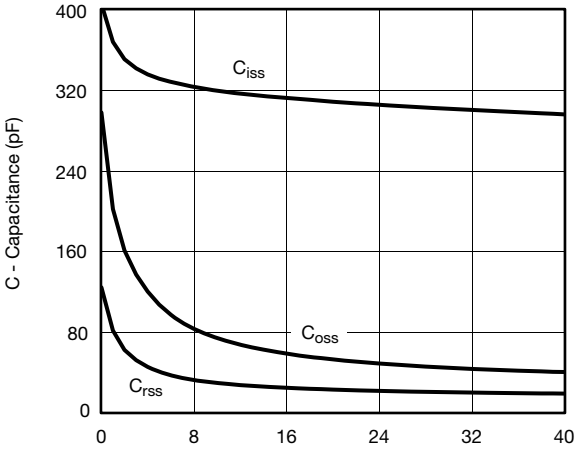
Output Characteristics



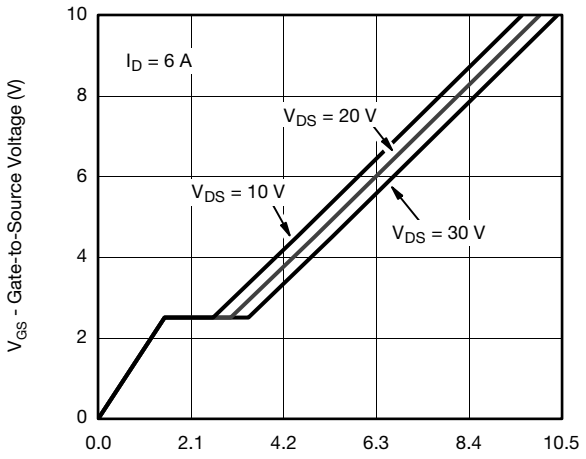
Transfer Characteristics



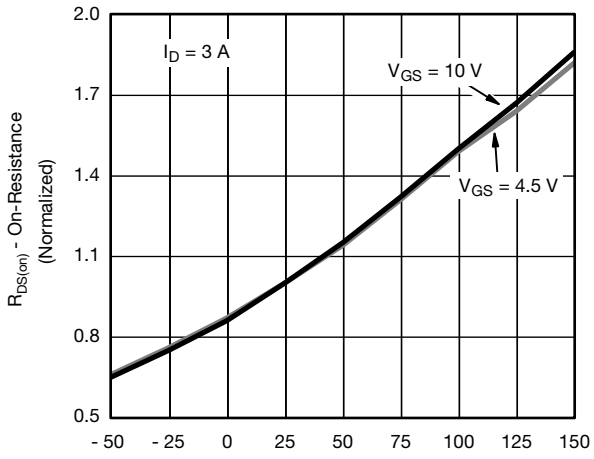
On-Resistance vs. Drain Current



Capacitance

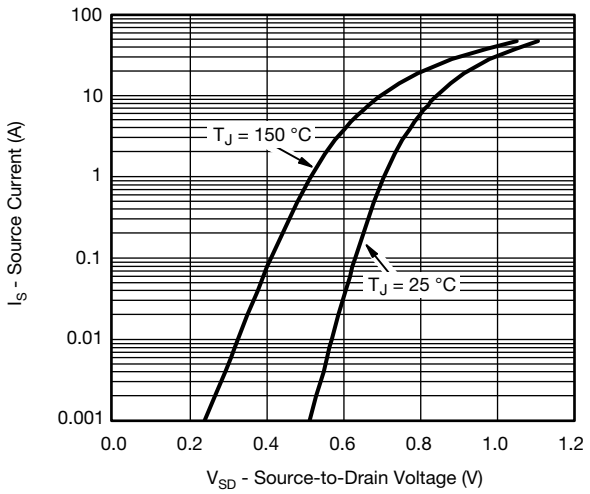


Gate Charge

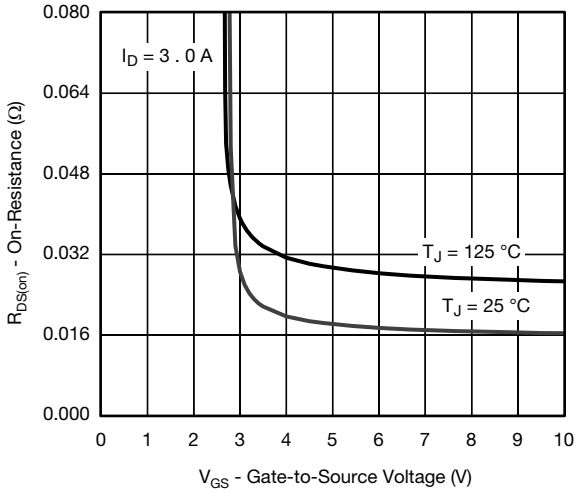


On-Resistance vs. Junction Temperature

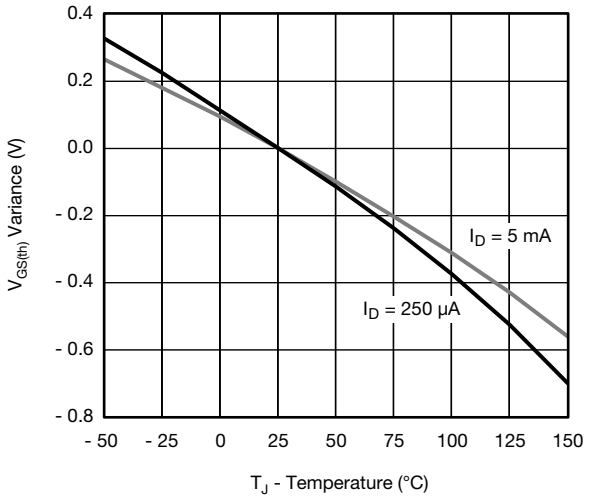
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



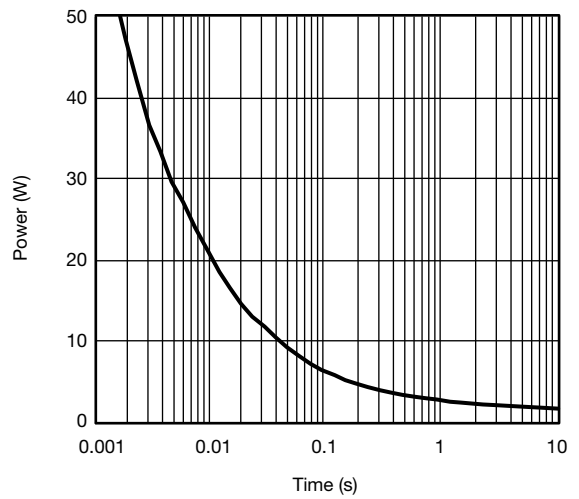
Source-Drain Diode Forward Voltage



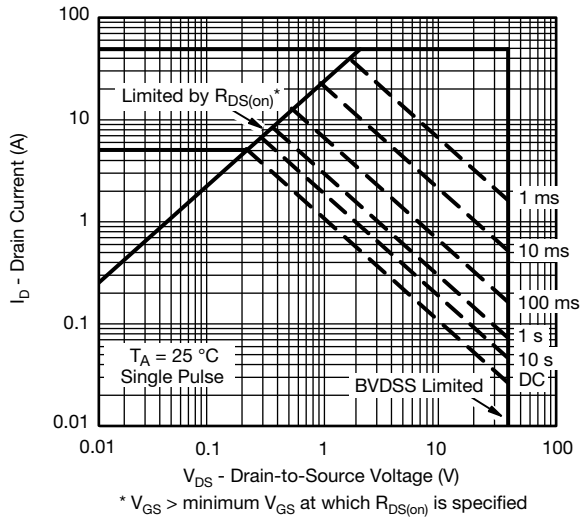
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

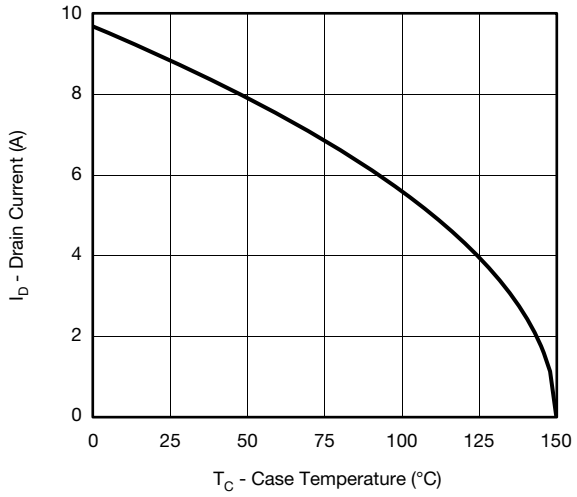


Single Pulse Power, Junction-to-Ambient

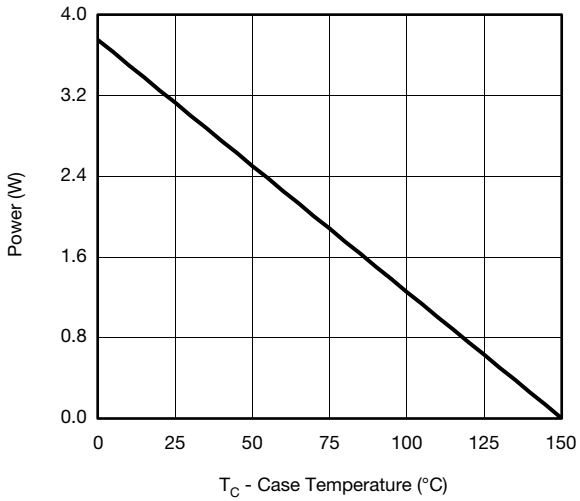


Safe Operating Area

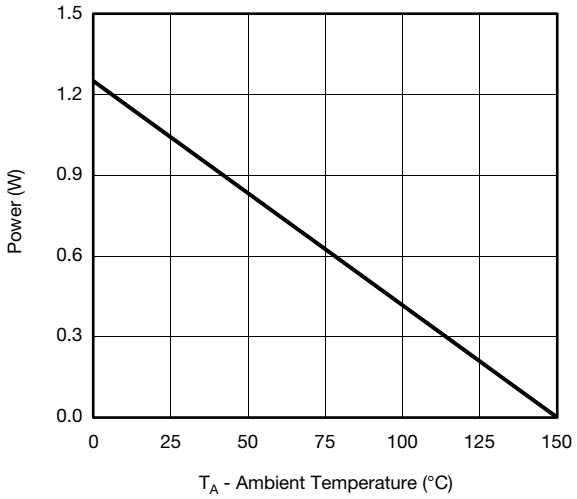
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



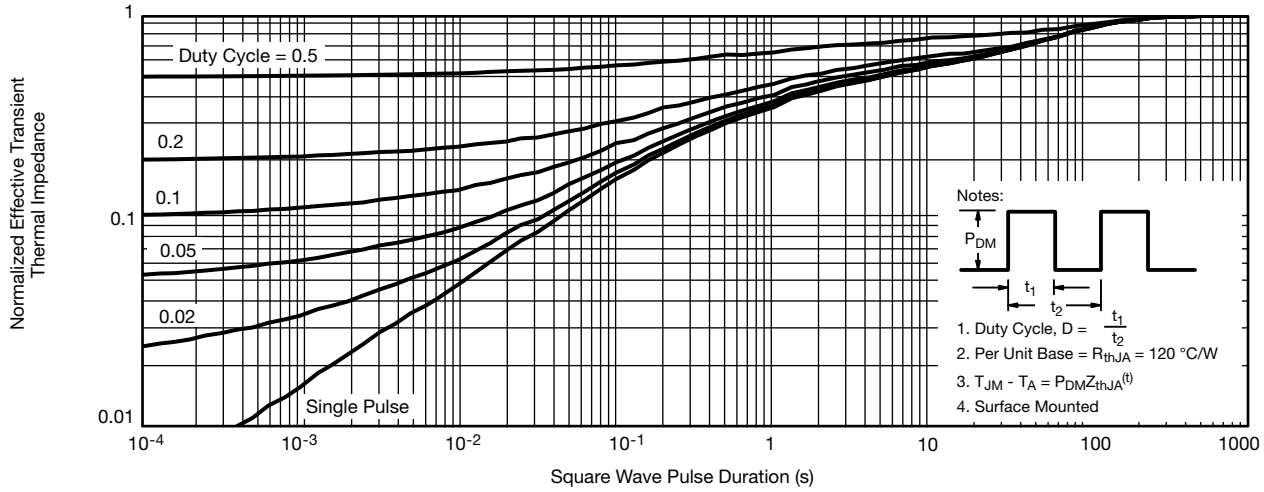
Power Derating, Junction-to-Foot



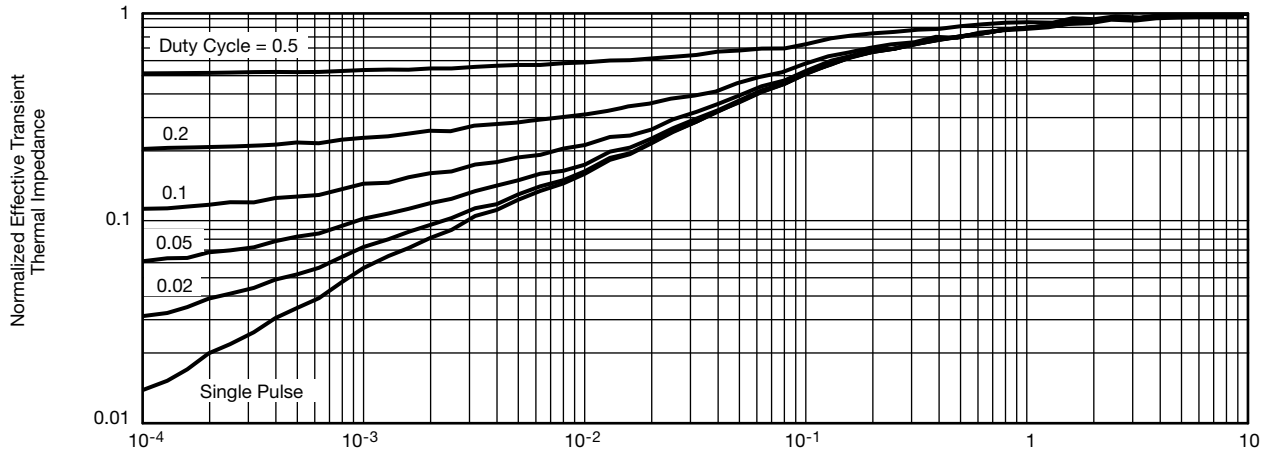
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

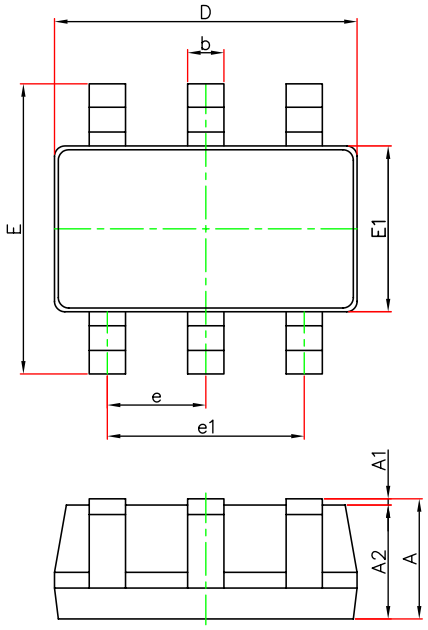


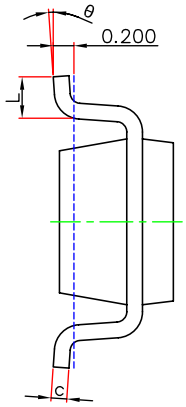
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

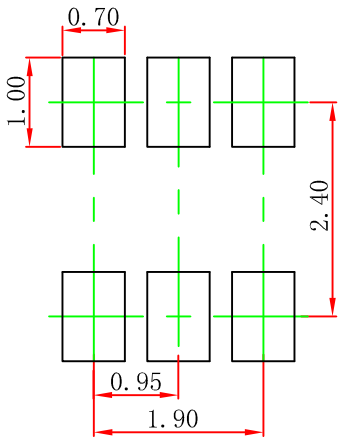
SOT-23-6L Package Outline Dimensions





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

SOT-23-6L Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

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